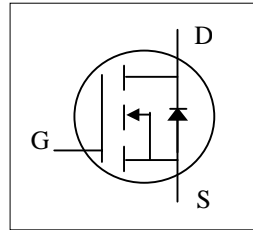




- ▼ Low Gate Charge
- ▼ Fast Switching Characteristics
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free

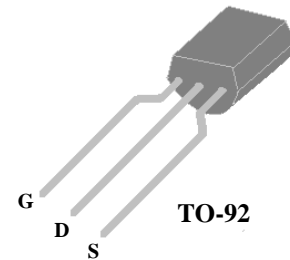


BV_{DSS}	700V
$R_{DS(ON)}$	13.5 Ω
I_D	160mA

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The TO-92 package is widely used for all commercial-industrial applications.



Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	700	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_A=25^\circ\text{C}$	Drain Current, V_{GS} @ 10V	160	mA
$I_D@T_A=100^\circ\text{C}$	Drain Current, V_{GS} @ 10V	100	mA
I_{DM}	Pulsed Drain Current ¹	300	mA
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	0.83	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient	150	$^\circ\text{C}/\text{W}$



AP01L60T-H-HF

Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	700	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =0.3A	-	-	13.5	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =0.3A	-	0.5	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =100mA	-	7	11	nC
Q _{gs}	Gate-Source Charge	V _{DS} =480V	-	1.4	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	3.4	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =300V	-	8	-	ns
t _r	Rise Time	I _D =1A	-	5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =10Ω	-	13	-	ns
t _f	Fall Time	V _{GS} =10V	-	9	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	260	420	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	20	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	3	-	pF
R _g	Gate Resistance	f=1.0MHz	-	3	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage	I _S =160mA, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =1A, V _{GS} =0V,	-	345	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	1	-	μC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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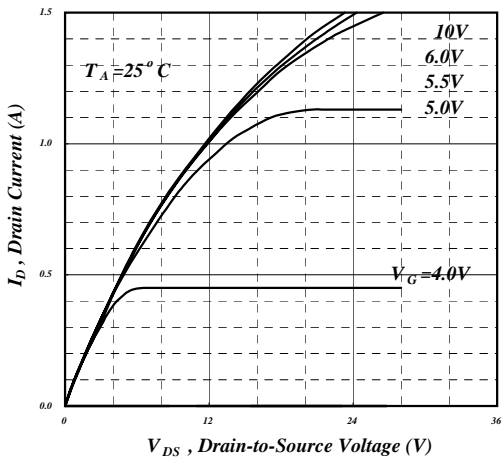


Fig 1. Typical Output Characteristics

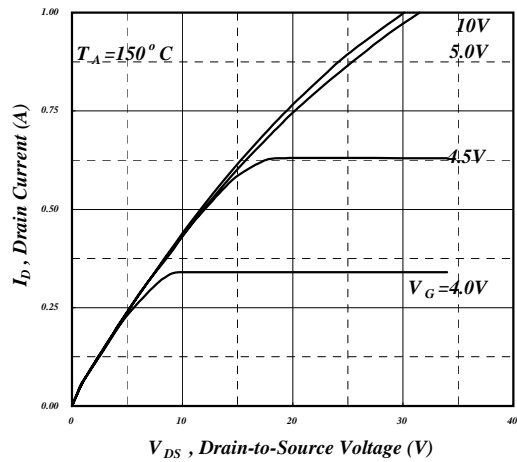


Fig 2. Typical Output Characteristics

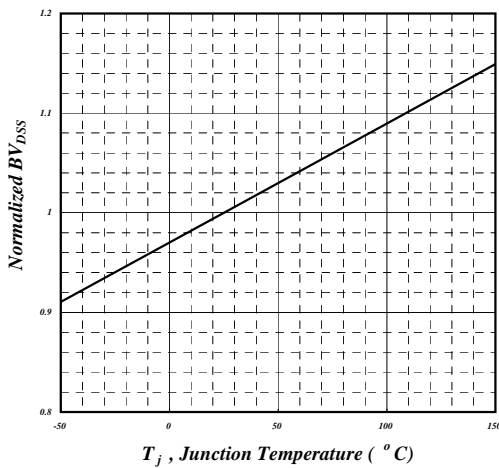


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

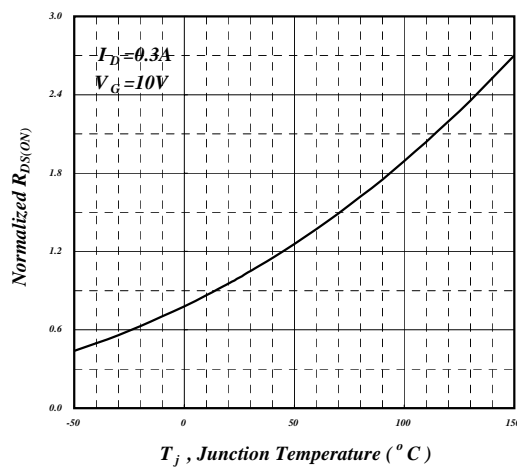


Fig 4. Normalized On-Resistance v.s. Junction Temperature

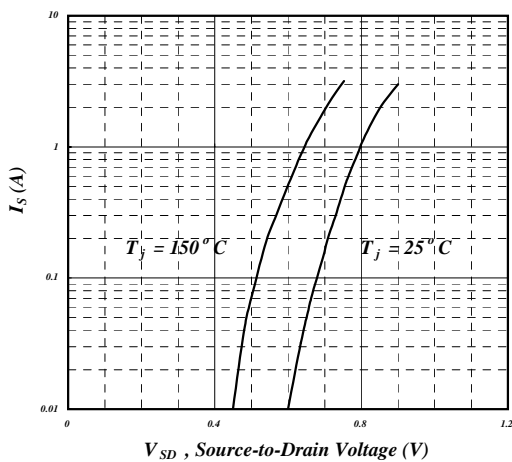


Fig 5. Forward Characteristic of Reverse Diode

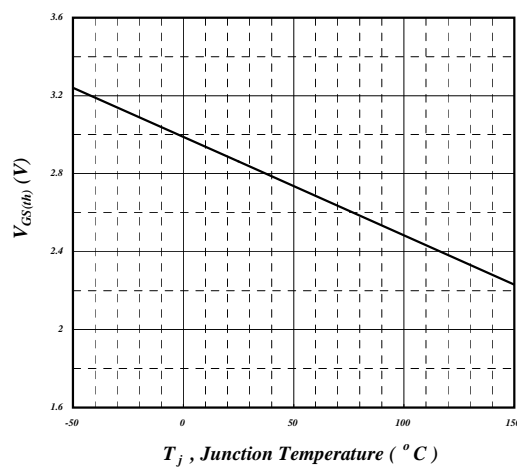


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

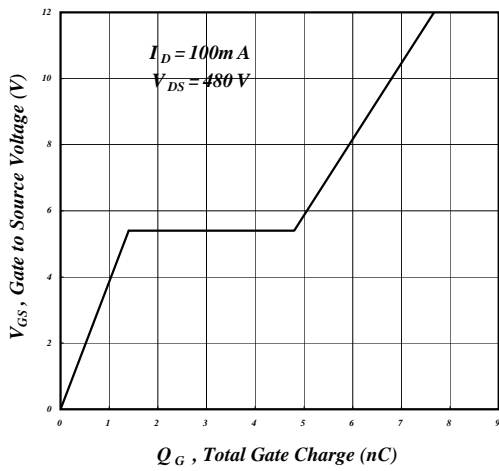


Fig 7. Gate Charge Characteristics

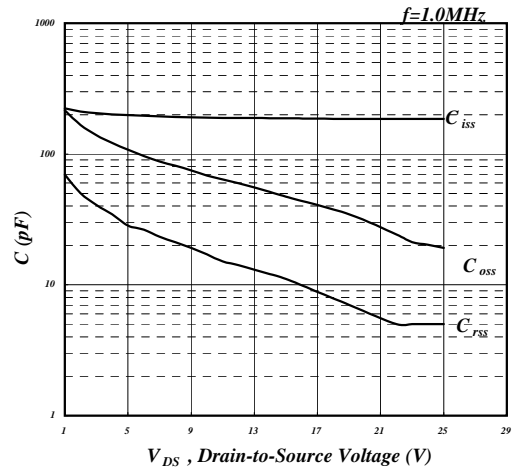


Fig 8. Typical Capacitance Characteristics

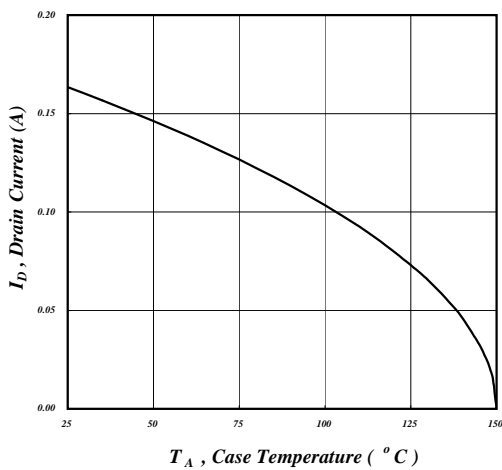


Fig 9. Maximum Drain Current v.s. Case Temperature

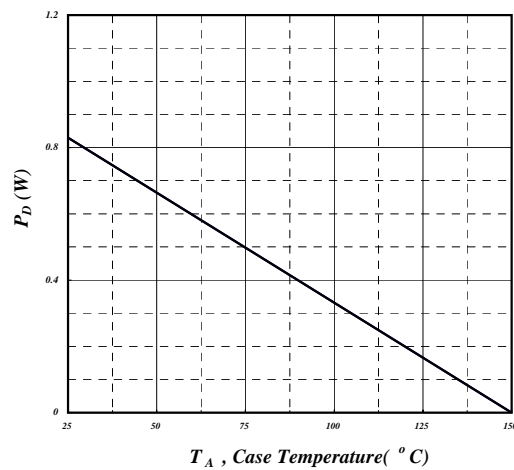


Fig 10. Typical Power Dissipation

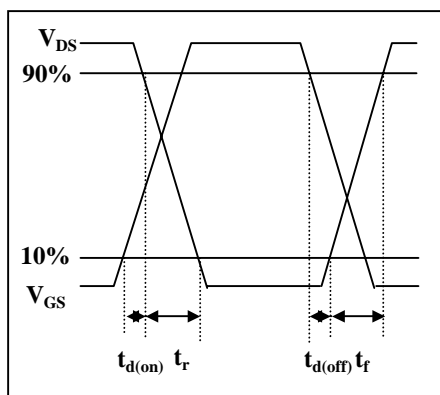


Fig 11. Switching Time Waveform

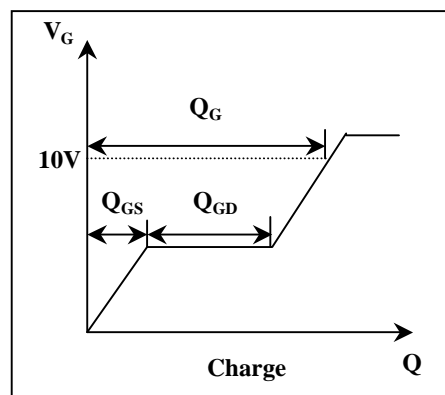


Fig 12. Gate Charge Waveform



MARKING INFORMATION

